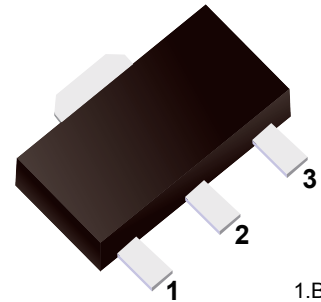


2SC4672

■ NPN Transistors

■ Features

- Low Saturation Voltage
- Excellent hFE Characteristics
- Complementary to 2SA1797



1.Base
2.Collector
3.Emitter

■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	60	V
Collector - Emitter Voltage	V _{CE0}	50	
Emitter - Base Voltage	V _{EB0}	6	
Collector Current - Continuous	I _c	2	A
Collector Power Dissipation	P _c	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

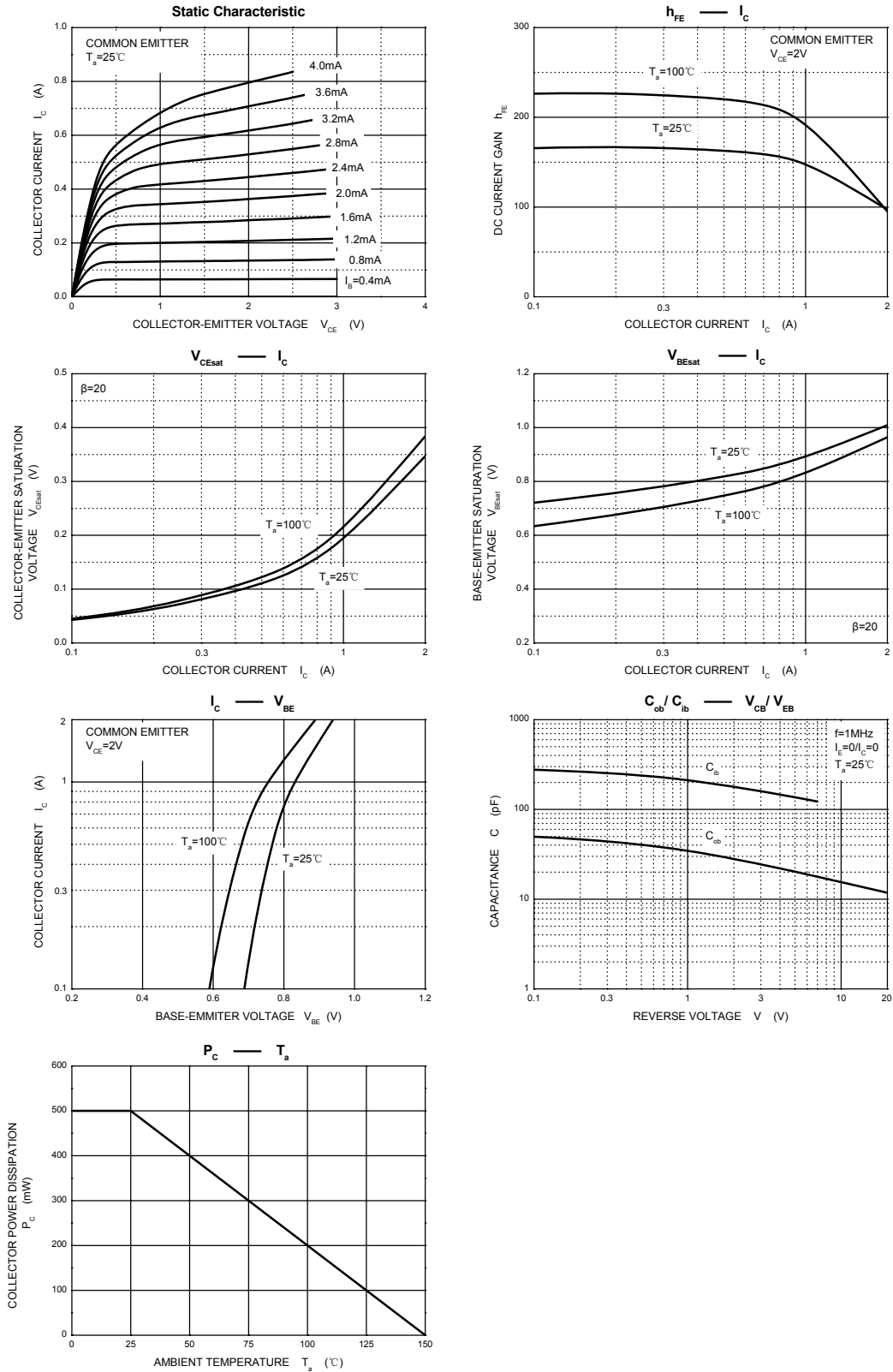
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 50 μA, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = 1 mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 50 μA, I _c = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 60V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _c =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =1A, I _B =50mA			0.35	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =1A, I _B =50mA			1.2	
DC current gain	hFE	V _{CE} = 2V, I _c = 500mA	82		390	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz		25		pF
Transition frequency	f _T	V _{CE} = 2V, I _c = 500mA, f=100MHz		210		MHz

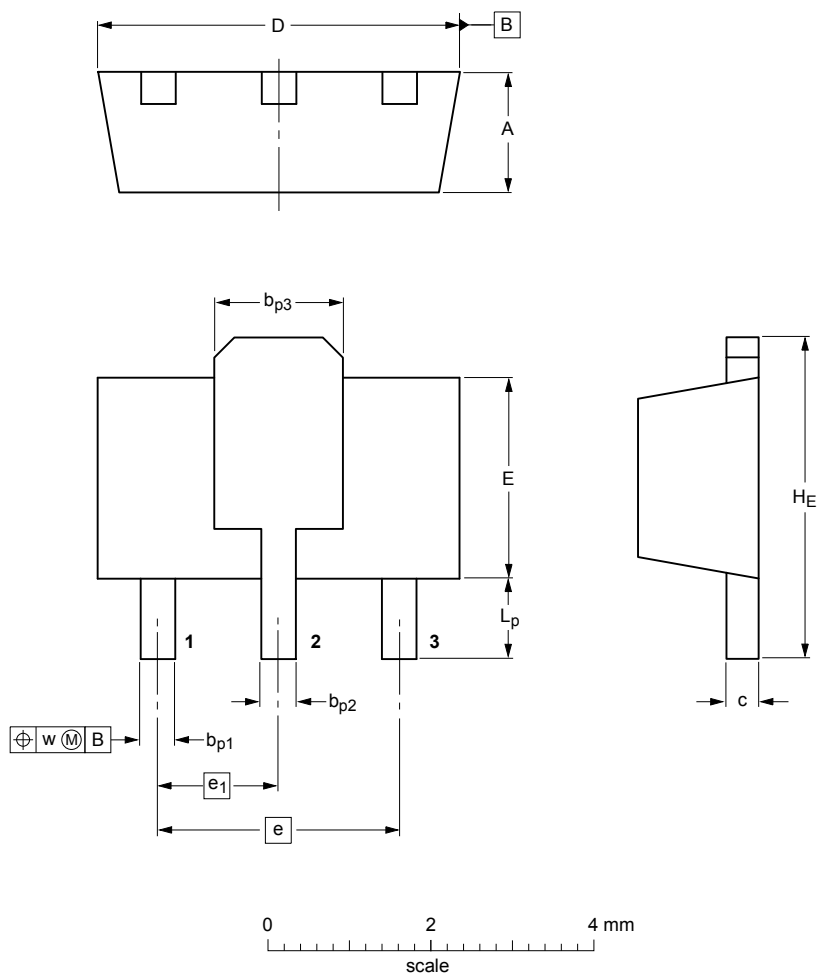
■ Classification of hfe

Type	2SC4672-P	2SC4672-Q	2SC4672-R
Range	82-180	120-270	180-390
Marking	DKP	DKQ	DKR

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					